

High Efficiency LEDs in ø 3 mm Clear Packages

Color	Type	Technology	Angle of half intensity $\pm\varphi$
High efficiency red	TLHR4900	GaAsP on GaP	17°
Soft orange	TLHO4900	GaAsP on GaP	
Yellow	TLHY4900	GaAsP on GaP	
Green	TLHG4900	GaP on GaP	

Description

The TLH.4900 series was developed for applications where high light output is required.

It is housed in a 3 mm clear plastic package. The small viewing angle of these devices provides a high brightness. All LEDs are categorized in luminous intensity groups. The green, yellow and orange LEDs are categorized additionally in wavelength groups.

That allows users to assemble LEDs with uniform appearance.

Features

- Choice of four bright colors
- Standard ø 3 mm (T-1) package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very small viewing angle
- Luminous intensity categorized
- Orange, yellow and green color categorized

Applications

Status lights
OFF / ON indicator
Background illumination
Readout lights
Maintenance lights
Legend light

Absolute Maximum Ratings

$T_{amb} = 25^\circ C$, unless otherwise specified

TLHR4900 , TLHO4900 , TLHY4900 , TLHG4900 ,

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage			V_R	6	V
DC forward current			I_F	30	mA
Surge forward current	$t_p \leq 10 \mu s$		I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 30^\circ C$		P_V	100	mW
Junction temperature			T_j	100	$^\circ C$
Operating temperature range			T_{amb}	-20 to +100	$^\circ C$
Storage temperature range			T_{stg}	-55 to +100	$^\circ C$
Soldering temperature	$t \leq 5 s$, 2 mm from body		T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient			R_{thJA}	700	K/W

Optical and Electrical Characteristics

$T_{amb} = 25^\circ C$, unless otherwise specified

High efficiency red (TLHR4900)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 10 \text{ mA}$, $I_{Vmin}/I_{Vmax} \geq 0.5$		I_V	6.3	13		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	612		625	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		635		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 17		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2	3	V
Reverse voltage	$I_R = 10 \mu A$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

Soft orange (TLHO4900)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 10 \text{ mA}$, $I_{Vmin}/I_{Vmax} \geq 0.5$		I_V	10	26		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	598		611	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		605		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 17		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu A$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

Yellow (TLHY4900)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 10 \text{ mA}$, $I_{V\min}/I_{V\max} \geq 0.5$		I_V	10	26		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	581		594	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		585		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		φ		± 17		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

Green (TLHG4900)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 10 \text{ mA}$, $I_{V\min}/I_{V\max} \geq 0.5$		I_V	16	37		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	562		575	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		565		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		φ		± 17		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

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Typical Characteristics ($T_{amb} = 25^\circ C$, unless otherwise specified)

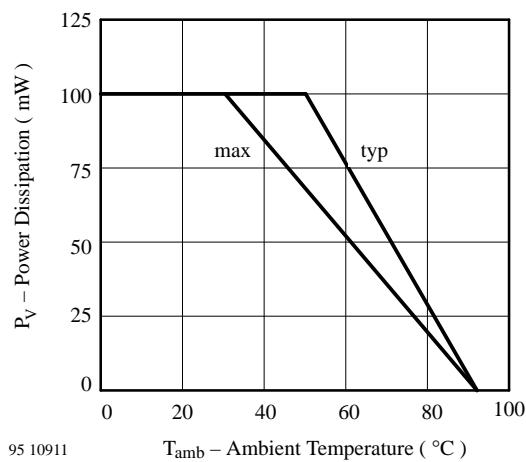


Figure 1. Power Dissipation vs. Ambient Temperature

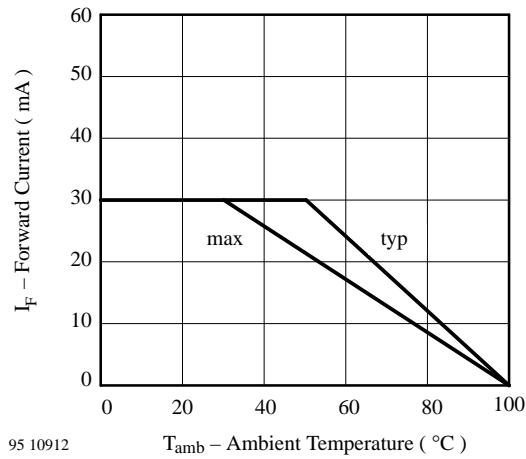


Figure 2. Forward Current vs. Ambient Temperature

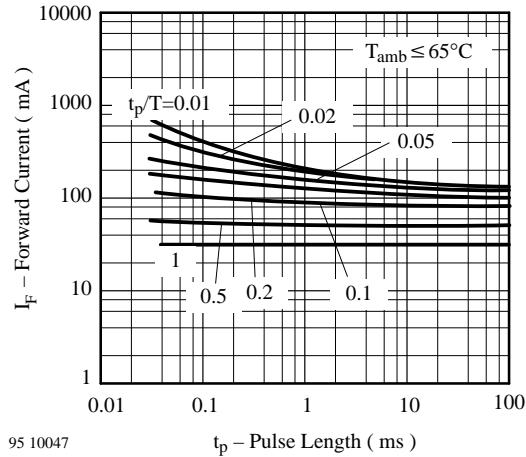


Figure 3. Forward Current vs. Pulse Length

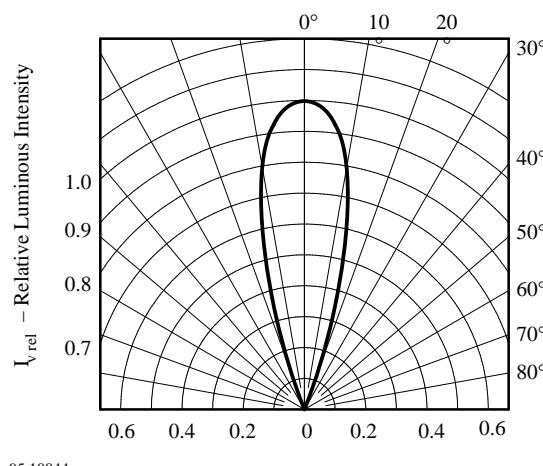


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

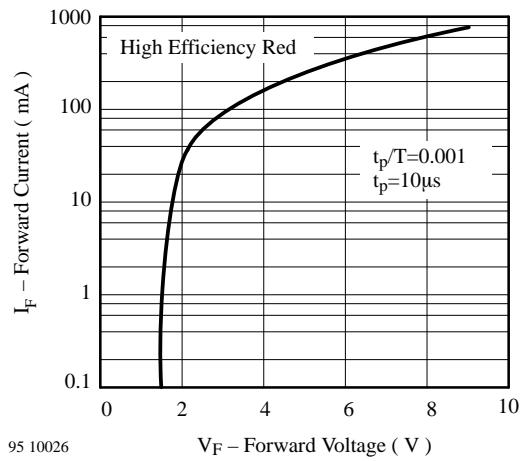


Figure 5. Forward Current vs. Forward Voltage

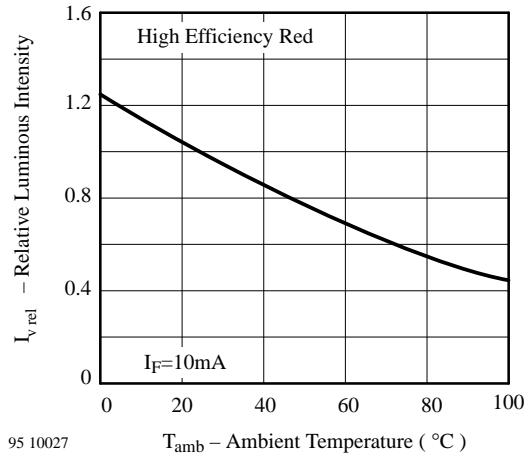


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

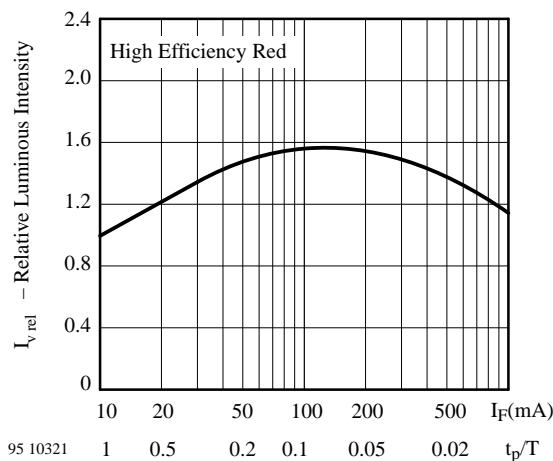


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

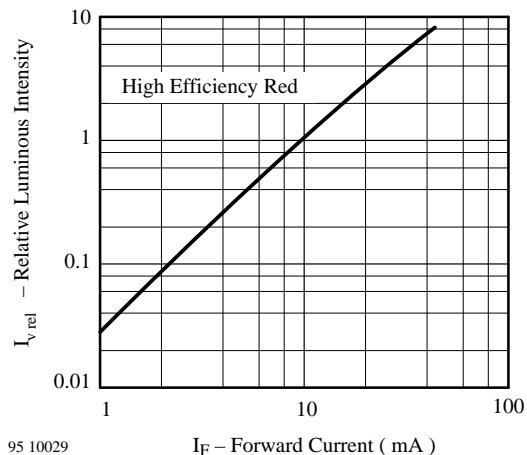


Figure 8. Relative Luminous Intensity vs. Forward Current

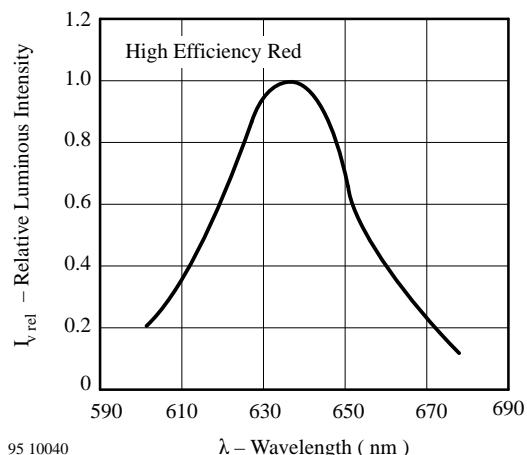


Figure 9. Relative Luminous Intensity vs. Wavelength

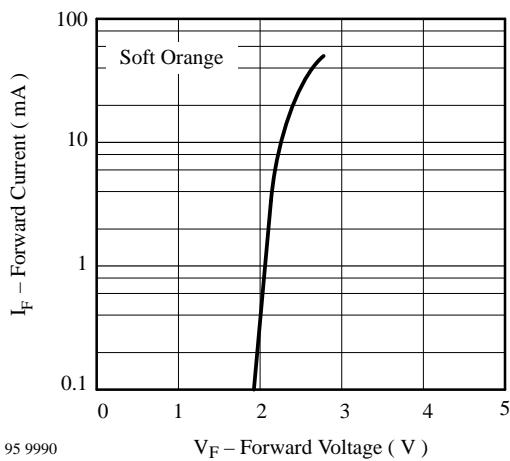


Figure 10. Forward Current vs. Forward Voltage

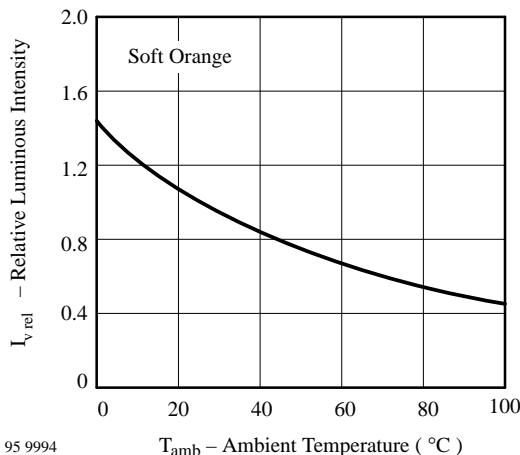


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

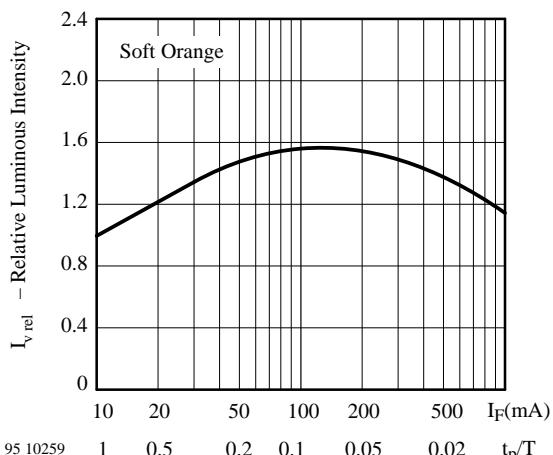


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

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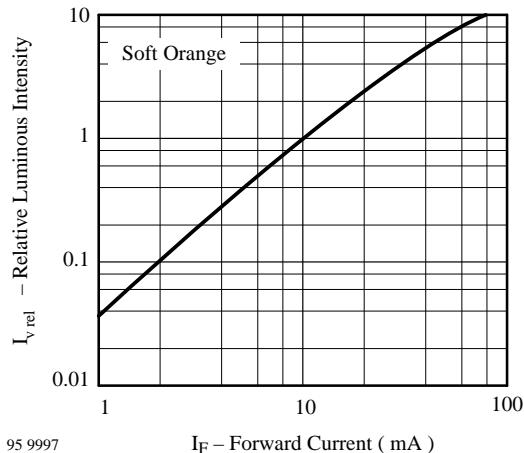


Figure 13. Relative Luminous Intensity vs. Forward Current

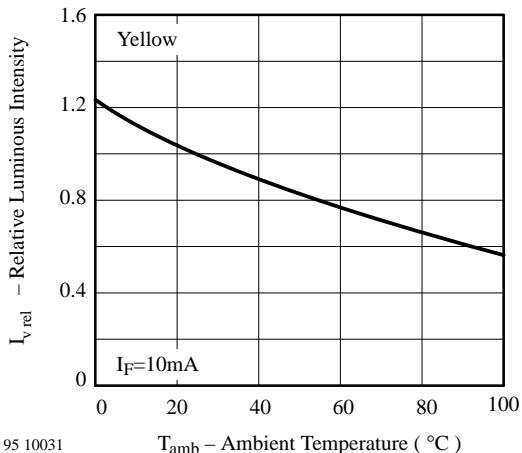


Figure 16. Rel. Luminous Intensity vs. Ambient Temperature

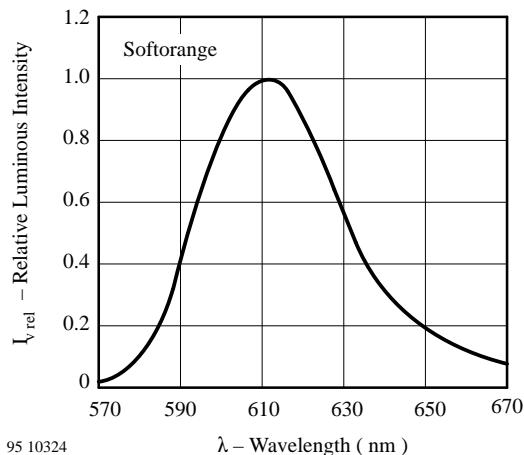


Figure 14. Relative Luminous Intensity vs. Wavelength

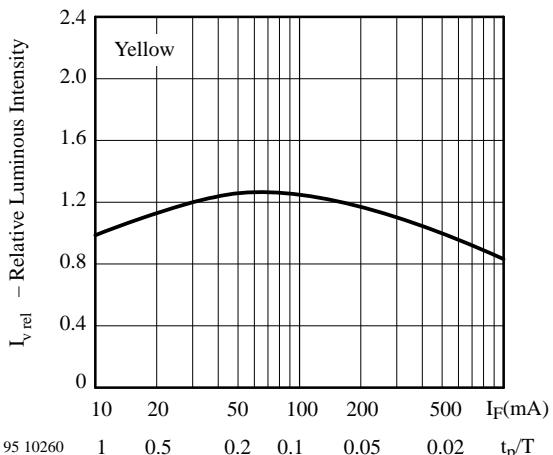


Figure 17. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

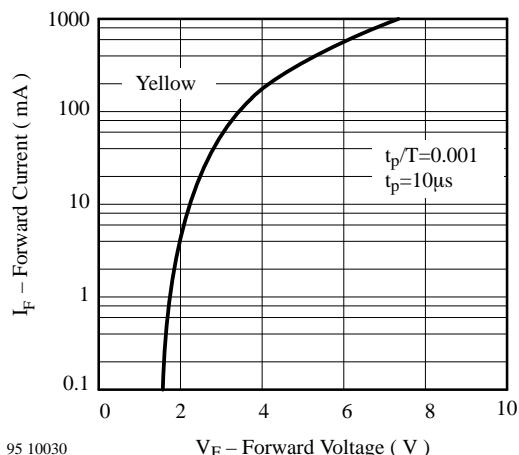


Figure 15. Forward Current vs. Forward Voltage

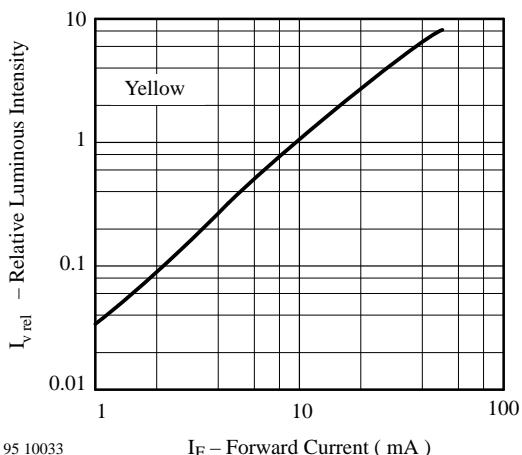


Figure 18. Relative Luminous Intensity vs. Forward Current

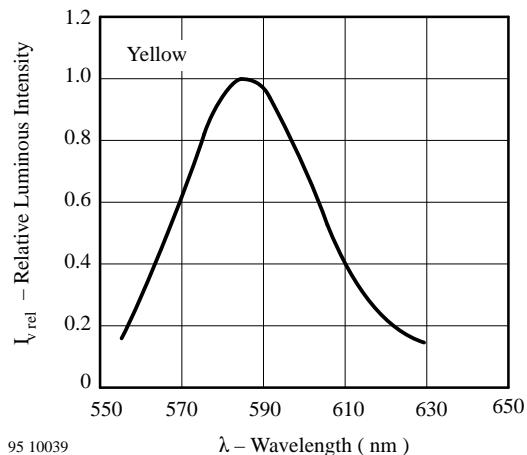


Figure 19. Relative Luminous Intensity vs. Wavelength

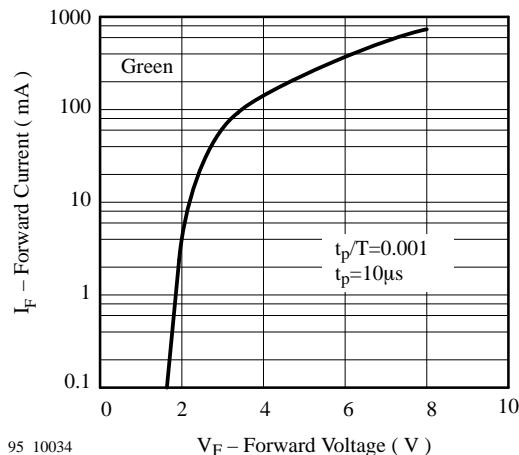


Figure 20. Forward Current vs. Forward Voltage

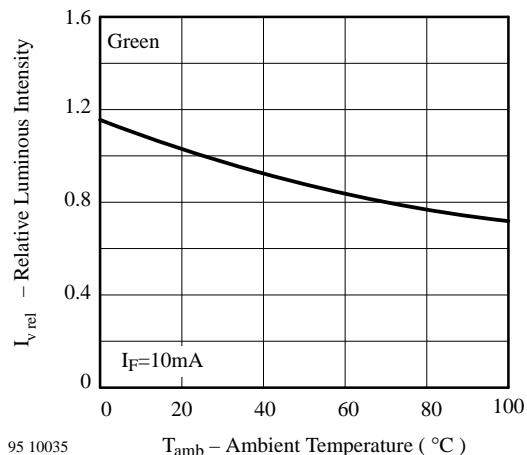


Figure 21. Rel. Luminous Intensity vs. Ambient Temperature

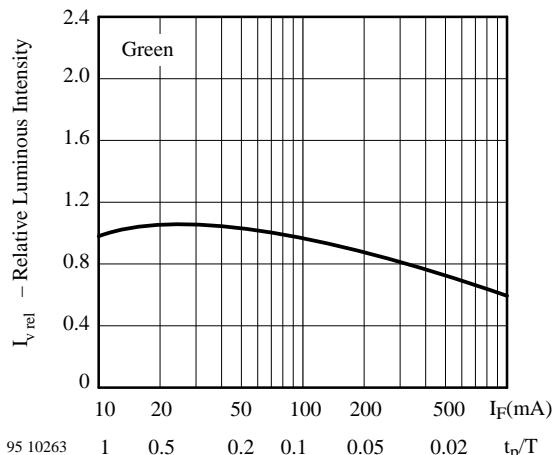


Figure 22. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

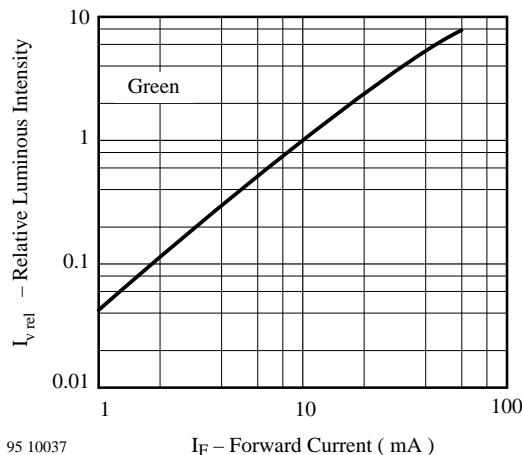


Figure 23. Relative Luminous Intensity vs. Forward Current

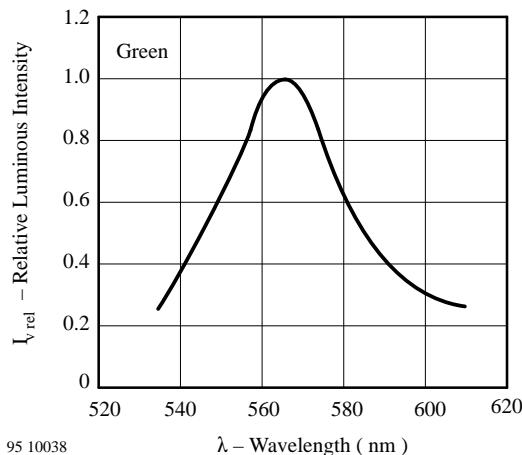
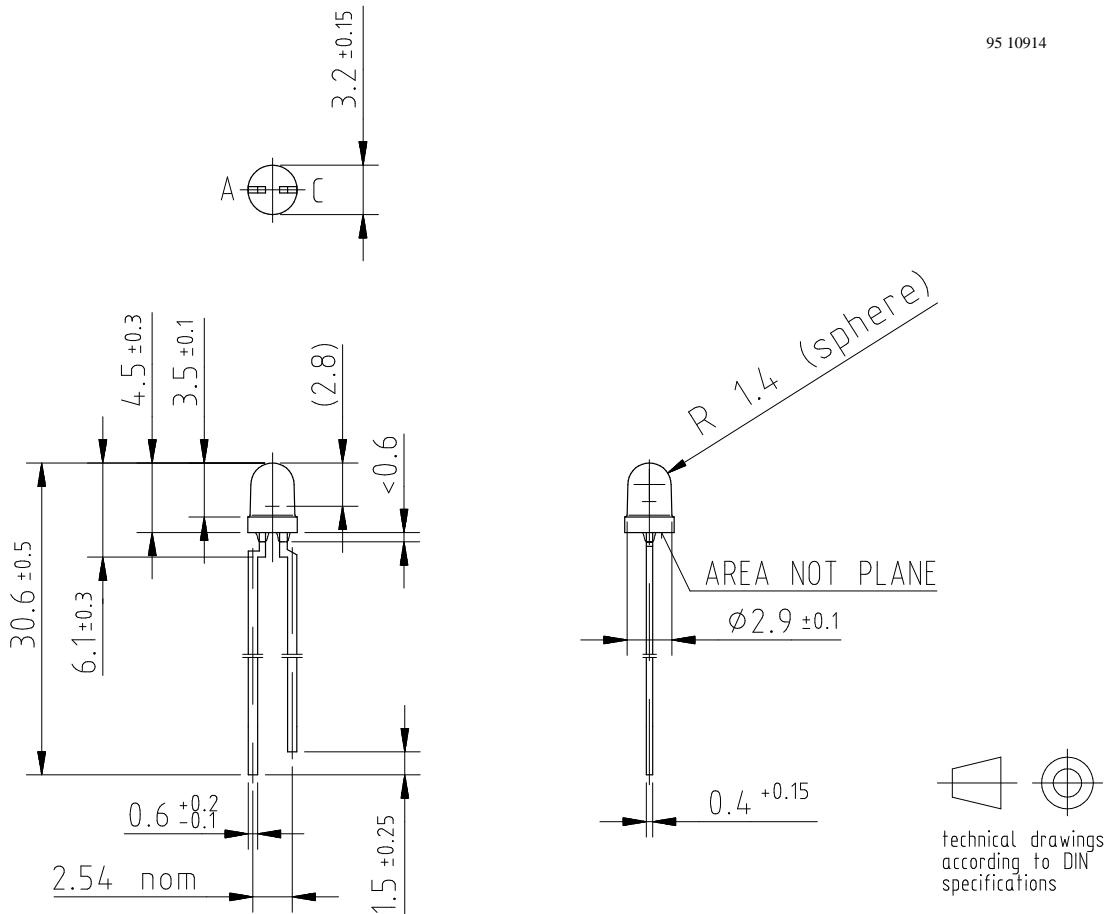


Figure 24. Relative Luminous Intensity vs. Wavelength

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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